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in the HF part. However this was restricted especially to areas of the surface which has a comparatively large layer spacing of for example. > 100  $\mu\text{m}$  to the HF structures. Tolerances in the conductor tracks could be accepted for these layer spacings.

- 5 A method for producing electric conductive structures on a conductive structure carrier is known from document EP-A-0 530 564 A564 with tin or a tin-lead alloy being used as a resist. A resist layer is applied to a metal layer and structured with the aid of a laser. The areas of the metal layer revealed are then removed by
- 10 etching.

- 15 In addition for example in particular the resist ma-N 2403 in the resist series ma-N 2400 from micro resist technology GmbH is known from a product information, Rev. : 2/01 for example, which as a resist, in comparison to chemical tin, has properties as a resist
- with regard to lasering in the laser structuring method, etching in the etch method and the minimum thickness with which it can be applied on a conductor carrier which at least correspond to those of chemical tin or an amorphous resist.

- 20 The object of the present invention is to specify a method for producing electric conductive structures for use in high frequency technology on a conductive structure carrier with layer spacings of significantly less than 100  $\mu\text{m}$  using microstrip conductors.

In accordance with the invention this object is achieved by a method featuring the steps specified in Claim 1.

- 25 Accordingly a combination of laser structuring methods and etching methods is used in connection with a resist with high adhesion which

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at least as regards the lasering in the laser structuring methods,  
the etching in the etching methods and the minimum thickness with  
which it can be applied to the conductive structure carrier, has  
properties which at least correspond to those of chemical tin or of  
5 an amorphous resist.

Chemical tin can be applied at a strength of around 1  $\mu\text{m}$ . An  
amorphous resist can even be applied at a strength of far less than  
20  $\mu\text{m}$ . The thinner a resist can be applied, the better it is for the  
current method. Previous resists had a layer thickness of far  
10 greater than 20  $\mu\text{m}$ . The far thinner resists allow laser treatment to  
be performed far more precisely. With an optimized fabrication  
process structures extending down into the 20 or 10  $\mu\text{m}$  range and  
lower are thus possible. These fine structures enable electric  
conductive structures that can be used with high-frequency  
15 technology to be embodied, replacing the conventional components  
which would otherwise be needed, with their corresponding  
disadvantages. In particular the conductor structures can

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The invention is explained in more detail below with reference to drawings. These show:

Figure 1 a basic procedural sequence of the method in accordance with the invention,

5 Figure 2 a part of a larger circuit board structure fabricated using the method in accordance with Figure 1, shown in cross-section with a conductor structure usable with high-frequency technology and a structure not usable with high-frequency technology,

10 Figure 3 a comparison in size between a conductor structure in accordance with the invention and in accordance with a corresponding conventional technology,

15 Figures 4 to 7 the steps involved in producing a coil in accordance with the invention,

Figures 8 to 10a side view of three completed applications in a circuit board which have been implemented in accordance with the invention,

20 Figure 11 and 12 further applications in accordance with the invention,

Figures 13 to 16 Application examples in accordance with the invention in relation to a capacitor, a coil, a resistor and a moisture sensor.

25 The laser-structured Partial High Density Interconnection (PHDI) shown in Figure 1 shows a conductor structure carrier 1 (substrate, e.g. an FR4 circuit board), of which the surface is initially pre-treated in an appropriate manner so as to enable a thin layer 2 of chemical copper to be applied. In a subsequent electrolytic coating  
30 a further copper coating 3 is then applied, with a total coating thickness of up to 20  $\mu\text{m}$  in the current exemplary embodiment.

Subsequently a thin resist layer 4, here consisting of chemical tin, with a layer thickness of around 1  $\mu\text{m}$ , is applied.

The coating phase is followed by a structuring phase. The structuring is performed with a laser 5, as shown in Figure 1. In the structuring phase the chemical tin layer 4 is milled away with the laser 5 at those points at which the copper coating 3 below the chemical tin layer 4 is to be subsequently removed.

After the structuring phase, as already indicated, the revealed copper layer 3 is etched away. Finally the chemical tin layer still present is stripped away.

In Figure 2 the area at the top left shows an inventive conductor structure 6 whereas the area in the center is a conventional conductor structure 7.

The inventive conductor structure 6, which is a new HF structure, features coating gaps 8 of for example 30  $\mu\text{m}$ . By contrast the conventional conductor structure 7 features coating gaps 9 of for example 180  $\mu\text{m}$ .

Also shown in Figure 2 in connection with the new HF structures is an individual micro pass-through contacting 10 and a number of microstrip conductors 11 of high quality.

Figure 3 shows a visual comparison of the size of the surface areas when a specified line structure is implemented in accordance with the invention, that is in new technology 12, and in accordance with conventional, i.e. old technology 13.

Figures 4 to 7 illustrate the step-by-step implementation of a coil realized with microstrip conductors in accordance with the invention. Figure 4 here shows a copper surface with an edge length

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of 1 mm. The copper surface is structured with a laser in the individual production steps. In Figure 5 a coil shaped like a snail can already be seen. In Figure 6 the disruptive edge surfaces have been removed. In Figure 7 the coil is completed.

- 5 Figures 8 to 10 again show a side view of completed applications, based here on coils in each case. The shape and size of the Figures can be chosen at random. In the exemplary embodiment shown the most compact form was selected in each case.

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Figure 11 shows a possible application within the circuit board below a component.. In the form shown no component placement surface of the circuit board is needed. The coil could also be accommodated at any other points in the layout.

- 5 In detail a component 14 can be seen which is connected in a substrate L1 with a pad 15. Below the substrate L15 or the pad 8, in a substrate L2 in new technology a coiled conductor structure is implemented, as is also shown in Figure 8 for example. Below the substrate 2 and below the coiled conductor structure a substrate L3  
10 corresponding the substrate L1 is arranged.

- There is also an enlarged view of the section integrated into Figure 11 which shows an enlargement of the surface and the depth around pad 15. Here the enlarged section also shows an individual micro through-contacting 16, with which in the present exemplary  
15 embodiment through-contacting between substrate L1 and substrate L2 is established.

- Figure 12 shows an application as capacitors below a pad. The use of suitable insulating coatings and low coating thicknesses below them, e.g. up to 25  $\mu\text{m}$ , allow capacitors typically ranging up to 20 pF to  
20 be implemented in the smallest space. These capacitors have the additional advantage of barely having any inductive effect.

In detail a component 17 can be seen which is connected in a substrate L1 with a pad 18. Below the substrate L1 or below the pad  
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in a substrate L2 a conductor piece 19 is implemented in new technology, below this again in a substrate L3 a further pad 20 is arranged. In this case a first insulation layer 21 or a second  
5 insulation layer 22 are arranged between the substrate L1 and the conductor piece 19 on one side and between the conductor piece 19 and the substrate L3 on the other side. To summarize a multilayer capacitor between the pads 18, 20 is implemented with this arrangement.

10 A further enlarged sectional view is also integrated into Figure 12, as in Figure 11, showing an enlarged area of the depth and the surface around the pad 18.

Figure 13 shows a application relating to an HF capacitor. Figure 14 shows an application relating to an HF coil. Figure 15 shows an  
15 application relating to an HF resistor and Figure 16 shows an application relating to a moisture sensor.

The components in this case are realized in Figures 13, 14, 15 within a component area BE-F covered by a component next to a component pad surface BE-P which can also be seen as a component  
20 solder surface piece BE-A for an electrical connection with these said components.

In Figure 16 the component involved is shown on its own.

For the realization of the HF capacitor shown in Figure 13 with an HF structure 23 in PHDI technology a capacitor surface area 24 of  
25 around  $1 \text{ mm}^2$  is needed for the capacitor to have a capacitance of 1 pF. In this case high-quality conductor tracks 25 for the connection of the capacitor have a width of about  $20 \text{ }\mu\text{m}$  for example.

For the realization of the HF coil with an HF structure 26 in PHDI technology shown in Figure 14 a coil surface for an approx. 15 mm long stripline is needed which is realized with high quality with a  
5 conductor track 27.

A micro through-contacting 28 with a diameter of 0.08 mm is implemented for a midpoint connection of the coil.

For the realization of the HF resistor shown in Figure 15 a first copper layer for a first connection surface 29 and a second copper  
10 layer for a second connection surface 30 are implemented, between which a prespecified foil type is interleaved.

The connection surfaces 29, 30 combined as surfaces 32 are high-quality surfaces. Resistance values of the HF resistor are determined using the interleaved foil type and the connection  
15 surfaces. The calibration is undertaken in PHDI technology.

The exemplary embodiment in accordance with Figure 15 finally shows a conductor track 33 for the first connection and a conductor track 34 for the second connection of the HF resistor.

The moisture sensor depicted in Figure 16 is shown at two points in  
20 time. In the upper part of Figure 16 is the moisture sensor is shown before the laser process whereas in the lower part of Figure 16 it is shown after the laser process.

Before the laser process there only exists one high-quality surface 35 into which conductor tracks 36 with a high-quality width are  
25 incorporated with the laser process. The width in the exemplary embodiment shown is at least 25  $\mu\text{m}$ .



For the moisture sensor in Figure 16 conductor tracks 37 are realized for its connection which in the exemplary embodiment shown have a width of 0.1 mm.

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## Patent claims

1. Method for producing electric conductive structures for use in high frequency technology on a conductive structure carrier, in  
5 which steps in accordance with a laser structuring method and an etching method are combined using a resist, which at least as regards the lasering in the laser structuring method, the etching in the etching method and the minimum thickness with which it can be applied to the conductive structure carrier, has properties which at  
10 least correspond to those of chemical tin or an amorphous resist.
2. Method in accordance with Claim 1, characterized in that an FR 4 carrier material is used as a conductive structure carrier.
3. Method in accordance with Claim 1 or 2, characterized in that chemical tin or an amorphous resist is used as a resist.
- 15 4. Method in accordance with one of the previous claims, characterized in that at least in an environment of electric conductive structures usable with high-frequency technology at least large-area remaining electrical conductor structures can be removed.

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FIG 1

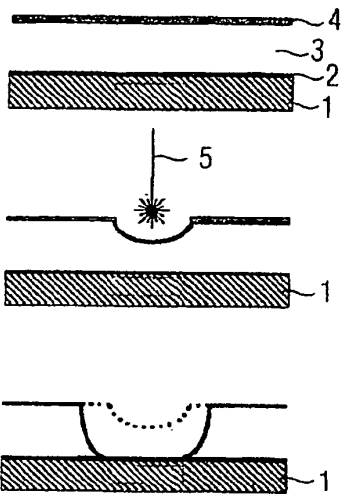


FIG 2

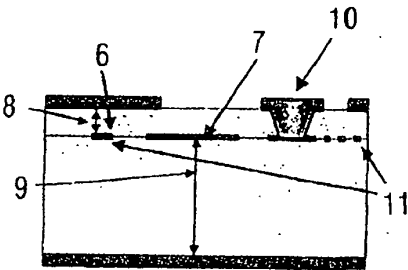
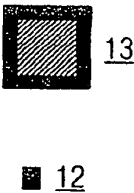


FIG 3

Area comparison



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FIG 4

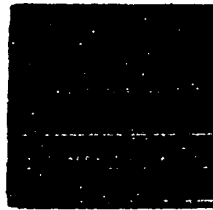


FIG 5

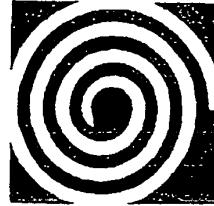


FIG 6



FIG 7



FIG 8



FIG 9



FIG 10



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FIG 11

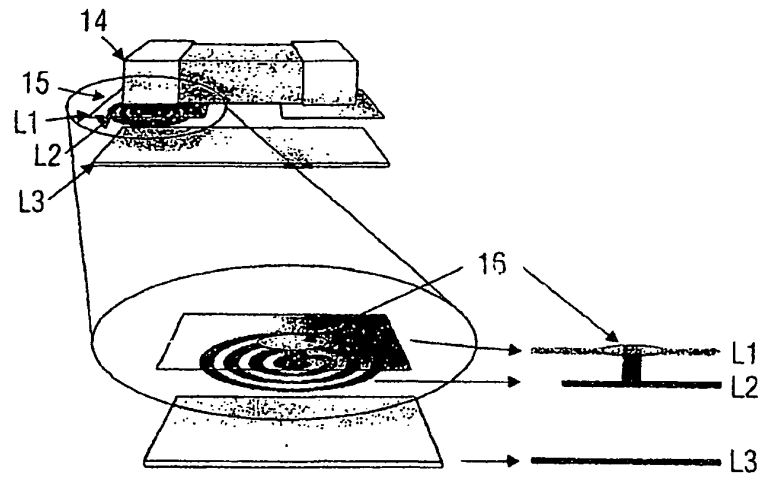
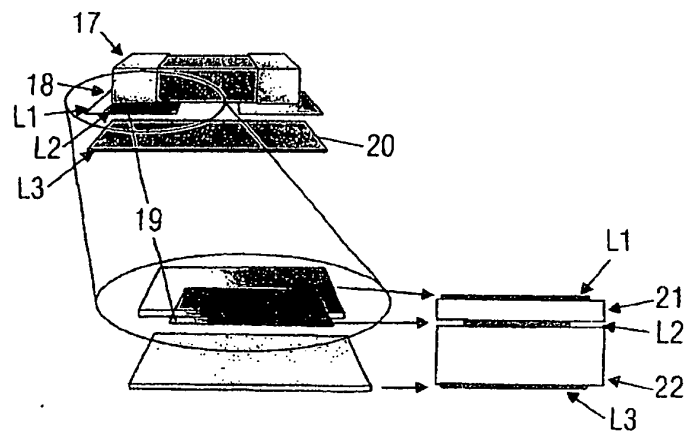


FIG 12



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FIG 13

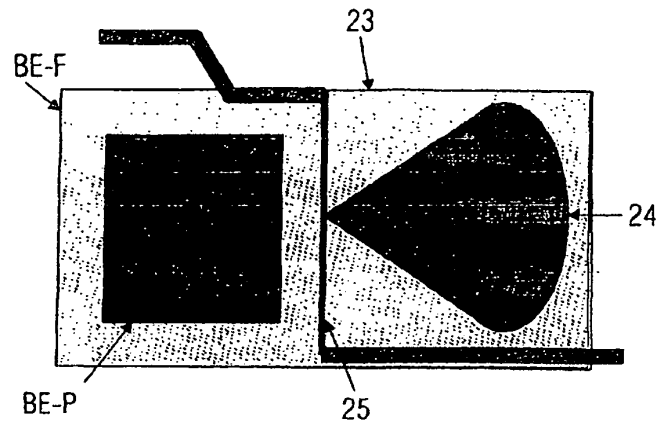
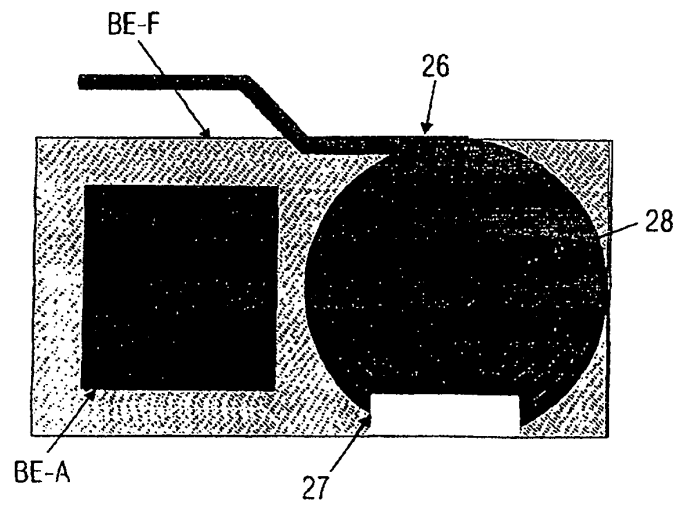


FIG 14



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FIG 15

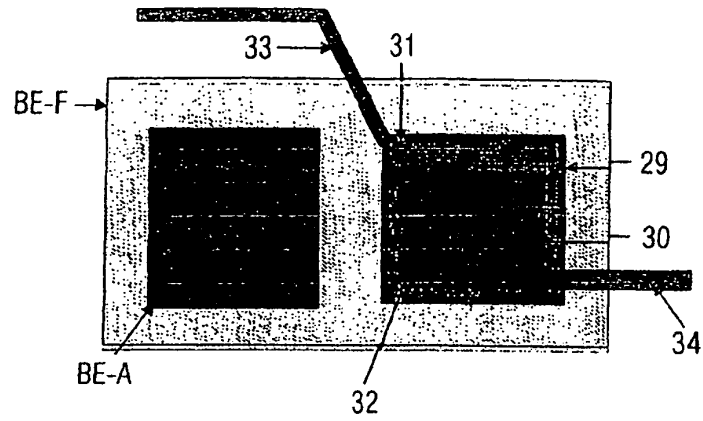
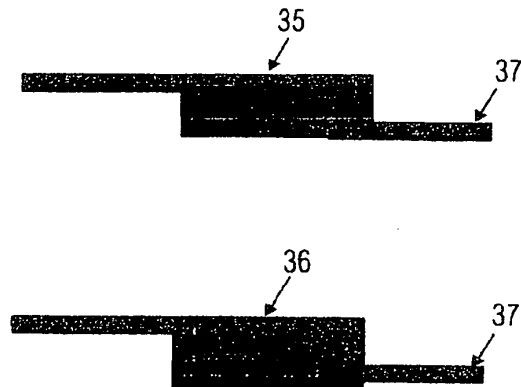


FIG 16



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